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- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce)
 <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} and Power-Up 3-State Support Hot Insertion
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN74LVT245B D	J OR W PACKAGE B, DW, OR PW PACKAGE IP VIEW)
DIR [1	20] V _{CC}
A1 [2	19] OE

ן אוט	11	20] ∧C(
A1 [2	19] <u>O</u> E
A2 [3	18] B1
A3 [4	17] B2
A4 [5	16] B3
A5 [6	15] B4
A6 [7	14] B5
A7 [8	13] B6
A8 [9	12] B7
GND [10	11] B8

SN54LVT245B . . . FK PACKAGE (TOP VIEW)

	A2 A1 OE OE	
A3	P 7	B1
A3 A4 A5 A6 A7	5 17	B2
A5	6 16	B3
A6		Β4
A7		B5
	9 10 11 12 13	
	A8 GND B8 B7 B6 B6	

description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable (\overline{OE}) input can be used to disable the devices so the buses are effectively isolated.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN54LVT245B is characterized for operation over the full military temperature range of -55° C to 125° C. The SN74LVT245B is characterized for operation from -40° C to 85° C.



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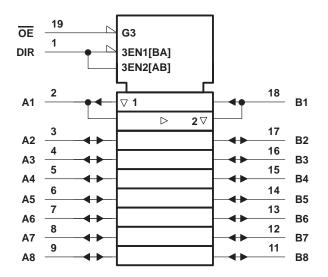
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FUNCTION TABLE

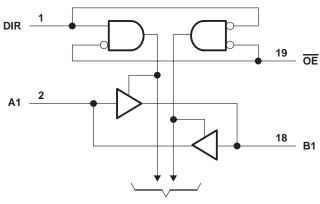
INP	UTS	OPERATION
OE	DIR	OPERATION
LL		B data to A bus
L	н	A data to B bus
н	Х	Isolation

logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



To Seven Other Channels



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} Input voltage range, V _I (see Note 1) Voltage range applied to any output in the high-impedance	
or power-off state, V _O (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, VO (see Note 1)	-0.5 V to V _{CC} + 0.5 V
Current into any output in the low state, I _O : SN54LVT245B	96 mA
SN74LVT245B	128 mA
Current into any output in the high state, I _O (see Note 2): SN54LVT245B	48 mA
SN74LVT245B	
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	
Package thermal impedance, θ_{JA} (see Note 3): DB package	
DW package	
PW package	
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This current flows only when the output is in the high state and $V_{O} > V_{CC}$.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LV	T245B	SN74LV	UNIT		
			MIN	MAX	MIN	MAX	UNIT
V _{CC} Supply voltage				3.6	2.7	3.6	V
VIH	High-level input voltage		2	N	2		V
VIL	Low-level input voltage					0.8	V
VI	Input voltage					5.5	V
ЮН	OH High-level output current					-32	mA
IOL	Low-level output current		202	48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled	30%	10		10	ns/V
$\Delta t / \Delta V_{CC}$	Power-up ramp rate		Q 200		200		μs/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			54LVT24	5B	SN	111117				
					түр†	MAX	MIN	TYP [†]	MAX	UNIT		
VIK		V _{CC} = 2.7 V,	lj = -18 mA			-1.2			-1.2	V		
		V _{CC} = 2.7 V to 3.6 V,	I _{OH} = -100 μA V _{CC} -0.2 V _C				V _{CC} -0.	2				
		V _{CC} = 2.7 V,	I _{OH} =8 mA	I _{OH} = -8 mA 2.4			2.4			V		
VOH		$V_{CC} = 3 V$	I _{OH} = -24 mA	2						v		
		VCC = 3 V	I _{OH} = -32 mA				2					
			I _{OL} = 100 μA			0.2			0.2			
		V _{CC} = 2.7 V	I _{OL} = 24 mA			0.5			0.5			
Va			I _{OL} = 16 mA			0.4			0.4	V		
VOL		$V_{CC} = 3 V$	I _{OL} = 32 mA			0.5			0.5	v		
		VCC = 3 V	I _{OL} = 48 mA			0.55						
			I _{OL} = 64 mA		4	N	0.55					
	Control inputs	V _{CC} = 3.6 V,	$V_I = V_{CC} \text{ or } GND$	±1					±1			
	Control inputs	V _{CC} = 0 or 3.6 V,	V _I = 5.5 V		A.	10			10			
lj –	A or B ports‡	V _{CC} = 3.6 V	V _I = 5.5 V		5	20			20	μA		
			$V_I = V_{CC}$		2	1			1			
			V _I = 0	C	5	-5			-5			
loff	-	V _{CC} = 0,	$V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5 \text{ V}$	2					±100	μA		
IOZH		V _{CC} = 3.6 V,	V _O = 3 V			5			5	μA		
IOZL		V _{CC} = 3.6 V,	V _O = 0.5 V			-5			-5	μA		
IOZPU		$\underline{V_{CC}} = 0$ to 1.5 V, $V_{O} = 0.5$ V to 3 V, $\overline{OE} = don't care$				±100*			±100	μA		
IOZPD		$\frac{V_{CC}}{OE} = 1.5 \text{ V to } 0, \text{ V}_{O} = 0$	V_{CC} = 1.5 V to 0, V _O = 0.5 V to 3 V, OE = don't care			±100*			±100	μA		
lcc		V _{CC} = 3.6 V,	Outputs high	high 0.19				0.19				
		$I_{O} = 0,$	Outputs low			5			5	5 mA		
		$V_{I} = V_{CC}$ or GND	Outputs disabled		0.19			0.19				
		V_{CC} = 3 V to 3.6 V, One Other inputs at V _{CC} or C				0.2			0.2	mA		
Ci		V _I = 3 V or 0			4			4		pF		
Cio		$V_{O} = 3 V \text{ or } 0$			9			9		pF		

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

[‡] Unused terminals are at V_{CC} or GND.

§ This is the increase in supply current for each input that is at the specified TTL-voltage level rather than V_{CC} or GND.



SN54LVT245B, SN74LVT245B 3.3-V ABT OCTAL BUS TRANSCEIVERS WITH 3-STATE OUTPUTS SCES004D – JANUARY 1995 – REVISED APRIL 2000

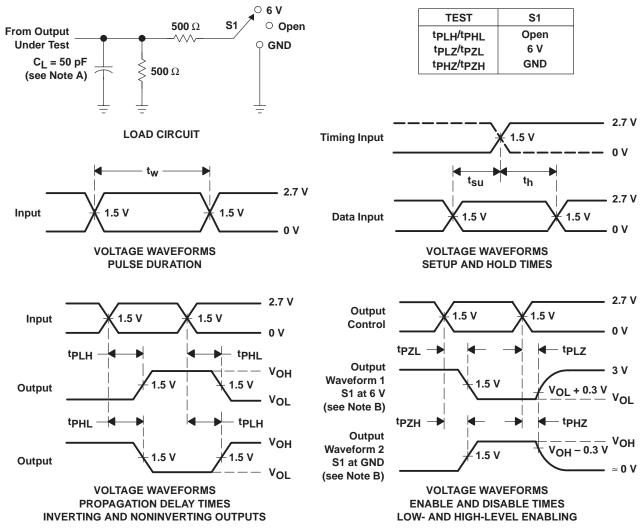
switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

			SN54LVT245B				SN74LVT245B							
PARAMETER	FROM (INPUT)	TO (OUTPUT)	×CC = ± 0.	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 3.3 V ± 0.3 V V _{CC} = 2.7		2.7 V	V _{CC} = 3.3 V ± 0.3 V			V _{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	MIN	TYP [†]	MAX	MIN	MAX			
^t PLH	A or B	B or A	1.1	3.7	1E	4.2	1.2	2.3	3.5		4	ns		
^t PHL	AOID	BUIA	1.1	3.7	3E	4.2	1.2	2.1	3.5		4	115		
^t PZH	OE	A or B	1.2	5.7	2	7.4	1.3	3.2	5.5		7.1	ns		
^t PZL	ÛE	AOIB	1.6	5.7		6.8	1.7	3.4	5.5		6.5	115		
^t PHZ	ŌĒ	A or B	2.1	6.2		6.8	2.2	3.5	5.9		6.5	ns		
^t PLZ		AUB	2.1	2 5.3		5.5	2.2	3.4	5		5.1	115		

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}C$.



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PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
- C. An input pulses are supplied by generators having the following characteristics. $rRK \ge 10$ km/z, ZO = 50.22, $r \ge 2.5$ ms, $r \ge 2.5$ ms

D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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